

Appl. No. : 067,634  
Filed : Herewith

36. (New) The process of Claim 22, wherein the substrate is a compound semiconductor.

37. (New) The process of Claim 36, wherein the substrate is GaAs.

38. (New) A method of growing a rare earth metal oxide thin film on a substrate from vapor-phase reactants comprising alternately introducing vapor-phase pulses of at least one rare earth metal source chemical and at least one oxygen source chemical into a reaction space containing a substrate, wherein the rare earth metal source chemical is a cyclopentadienyl compound.

#### REMARKS

The specification has been amended to add the priority claim for this application. A certified copy of the priority document is submitted herewith.

Claims 1-14 have been cancelled and new claims 15-38 have been added. The new claims are fully supported by the specification and claims as originally filed and do not add new matter.

Applicants submit that the present application is in condition for examination on the merits and respectfully request the same.

Respectfully submitted,

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